

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IRFR4105Z, IIRFR4105Z



- Static drain-source on-resistance: $R_{DS}(on) \leqslant 24.5 m_{\Omega}$
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

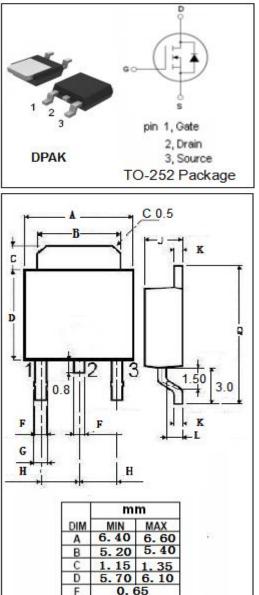
High Speed Power Switching

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

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SYMBOL	PARAMETER	VALUE	UNIT				
V _{DSS}	Drain-Source Voltage	55	V				
V _{GS}	Gate-Source Voltage	±20	V				
ID	Drain Current-Continuous	30	А				
I _{DM}	Drain Current-Single Pulsed	120	А				
PD	Total Dissipation @Tc=25°C 48		W				
Tj	Max. Operating Junction Temperature	175	°C				
T _{stg}	Storage Temperature	-55~175	°C				

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT	
Rth(j-c)	Channel-to-case thermal resistance	3.12	°C/W	
Rth(j-a)	Rth(j-a) Channel-to-ambient thermal resistance		°C/W	



0.

2.10

0.40

0.90

9.90

50

40

10

0.60

10

н

K

0



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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =250 μ A	55			V
V _{GS} (th)	Gate Threshold Voltage	VDS=VGS; I _D =250 µ A	2		4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =18A			24.5	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V			±0.2	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =55V; V _{GS} = 0V			20	μA
V _{SD}	Diode forward voltage	I _s =18A, V _{GS} = 0V			1.3	V

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